

Silicon PNP Power Transistors

2SA748

DESCRIPTION

- With TO-220 package
- Complement to type 2SC1398
- Large collector power dissipation

APPLICATIONS

- For medium power amplifier applicattions

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

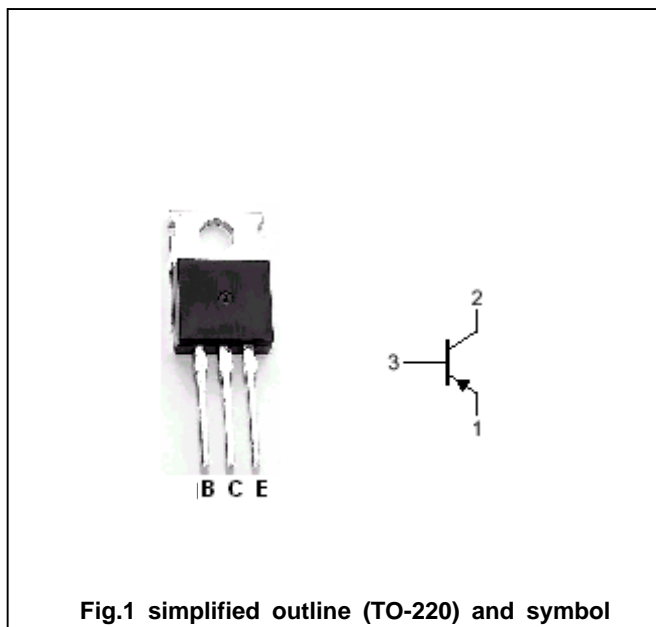


Fig.1 simplified outline (TO-220) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-70	V
V _{CEO}	Collector-emitter voltage	Open base	-50	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-2	A
I _{CM}	Collector current-peak		-3	A
P _C	Collector power dissipation	T _C =25	15	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Base-emitter breakdown voltage	I _C =-10mA, I _B =0	-50			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA, I _E =0	-70			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A; I _B =-0.1A		-0.6	-1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-2A; I _B =-0.2A		-1.0	-1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-40V; I _E =0			-1	μA
I _{CEO}	Collector cut-off current	V _{CE} =-20V; I _B =0			-100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-100	μA
h _{FE-1}	DC current gain	I _C =-0.1A; V _{CE} =-5V	30			
h _{FE-2}	DC current gain	I _C =-1A; V _{CE} =-5V	50		220	
f _T	Transition frequency	I _C =0.5A; V _{CE} =-5V		120		MHz

◆ h_{FE-2} Classifications

P	Q	R
50-100	80-160	120-220

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PACKAGE OUTLINE

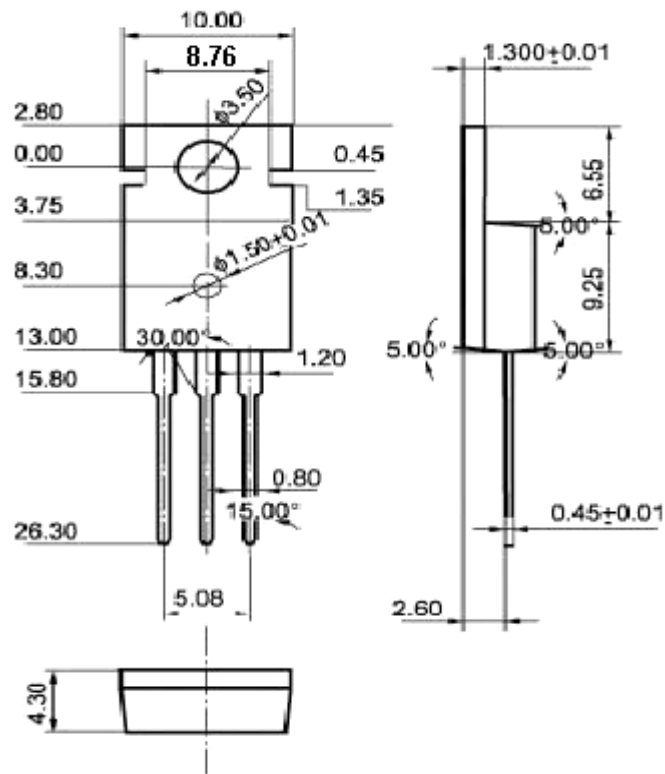


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)